



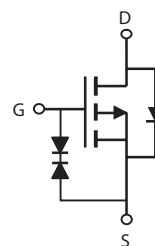
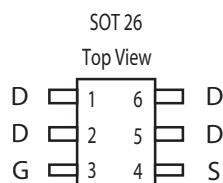
P-Channel Enhancement Mode Field Effect Transistor

PRODUCT SUMMARY

VDSS	ID	RDS(ON) (mΩ) Max
-20V	-2.8A	100 @ VGS=-4.5V
		105 @ VGS=-4.0V
		110 @ VGS=-3.7V
		121 @ VGS=-3.1V
		138 @ VGS=-2.5V

FEATURES

- Super high dense cell design for low RDS(ON).
- Rugged and reliable.
- Surface Mount Package.
- ESD Protected.



ABSOLUTE MAXIMUM RATINGS (TA=25°C unless otherwise noted)

Symbol	Parameter	Limit	Units
V _{DS}	Drain-Source Voltage	-20	V
V _{GS}	Gate-Source Voltage	±10	V
I _D	Drain Current-Continuous ^a	T _A =25°C	-2.8
		T _A =70°C	-2.2
I _{DM}	-Pulsed ^b	-10	A
P _D	Maximum Power Dissipation ^a	T _A =25°C	1.25
		T _A =70°C	0.8
T _J , T _{STG}	Operating Junction and Storage Temperature Range	-55 to 150	°C

THERMAL CHARACTERISTICS

R _{θJA}	Thermal Resistance, Junction-to-Ambient ^a	100	°C/W
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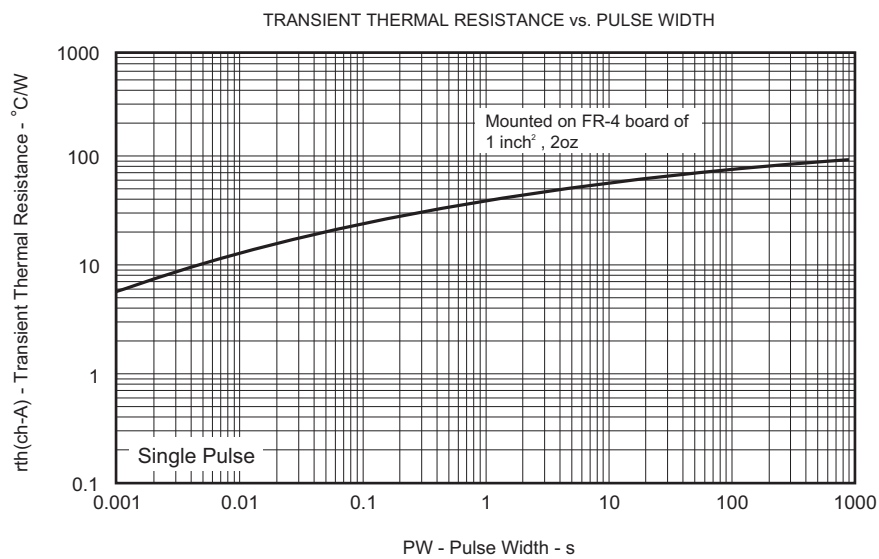
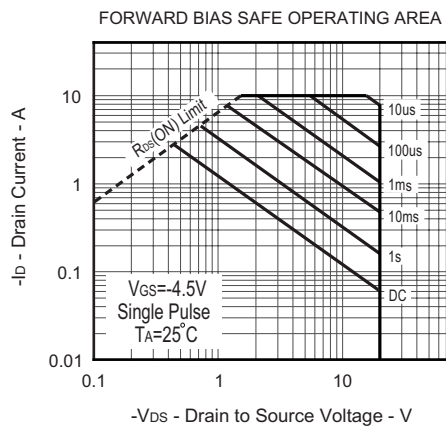
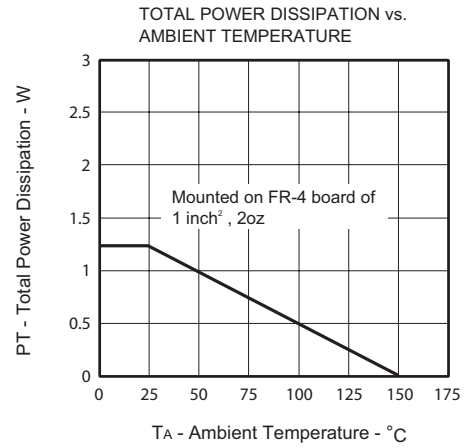
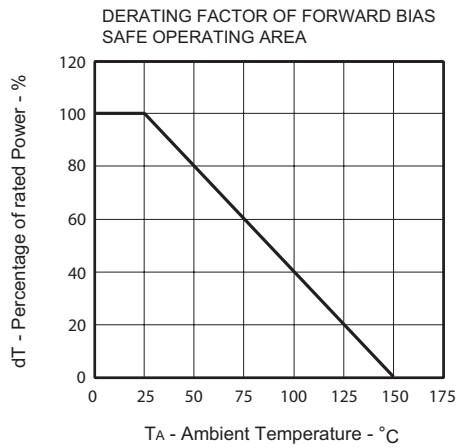
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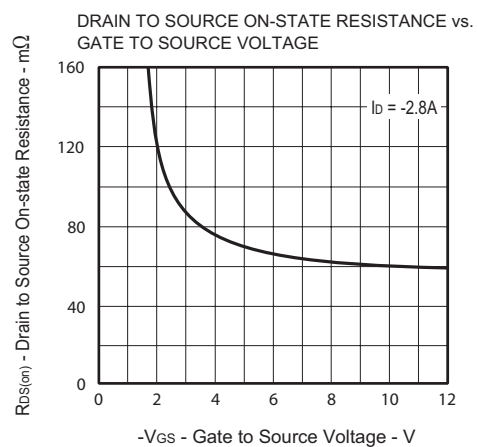
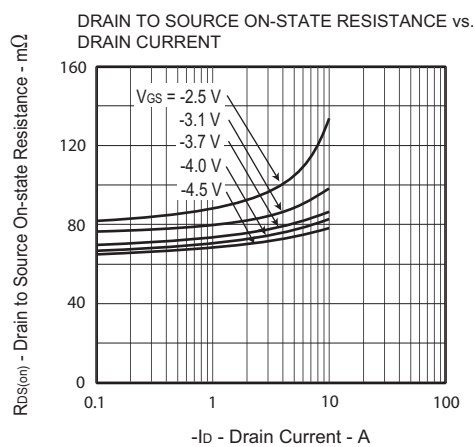
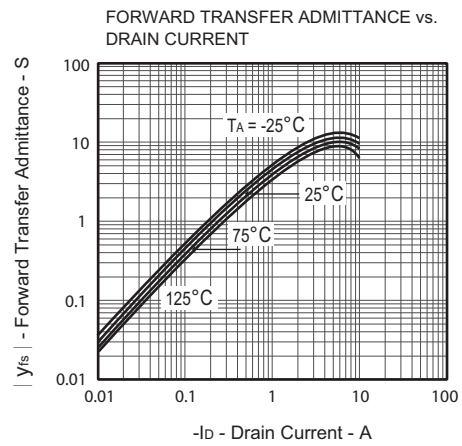
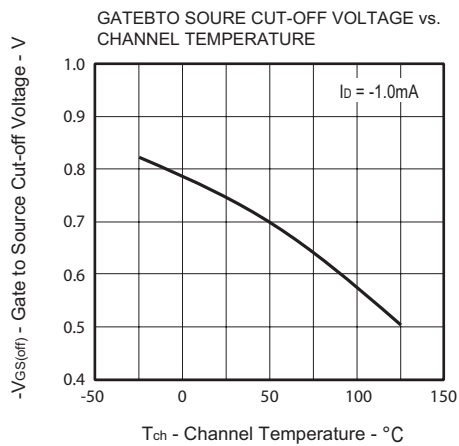
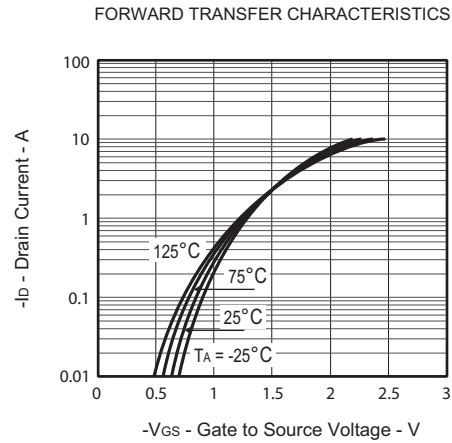
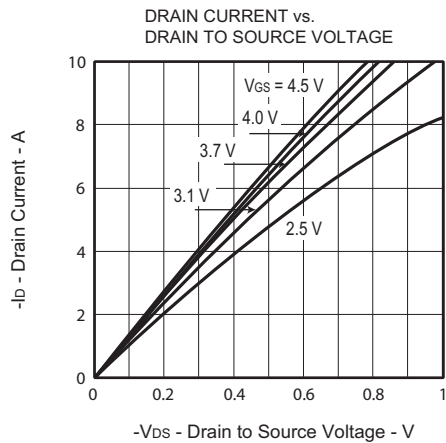
Ver 1.0

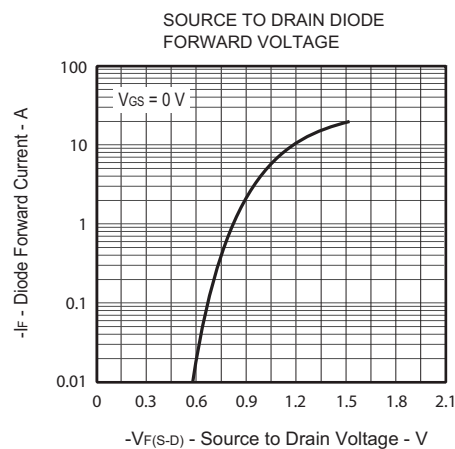
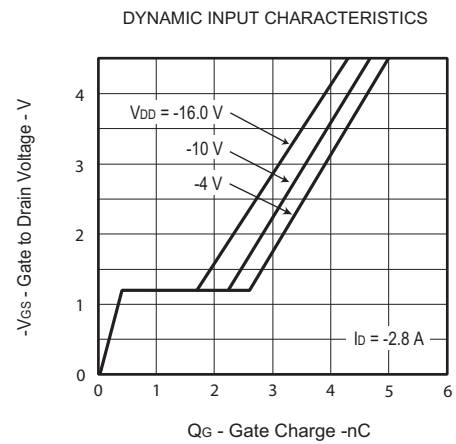
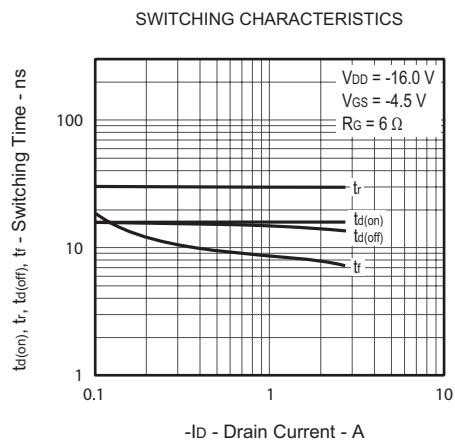
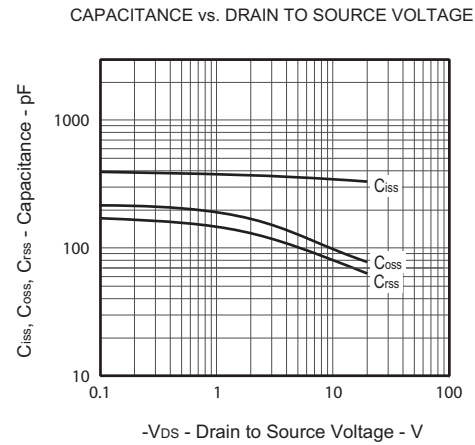
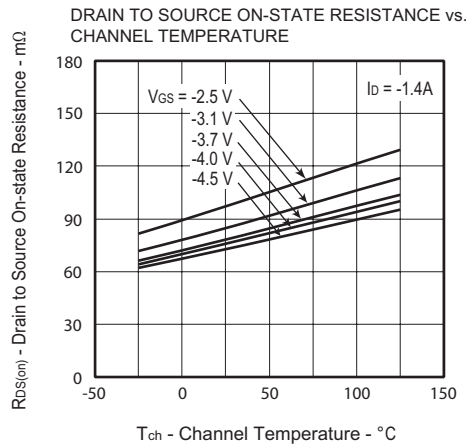
ELECTRICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =-250uA	-20			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-16V , V _{GS} =0V			1	uA
I _{GSS}	Gate-Body Leakage Current	V _{GS} = ±10V , V _{DS} =0V			±10	uA
ON CHARACTERISTICS						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-1mA	-0.5	-0.8	-1.5	V
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =-4.5V , I _D =-1.4A	62	76	100	m ohm
		V _{GS} =-4.0V , I _D =-1.4A	65	80	105	m ohm
		V _{GS} =-3.7V , I _D =-1.4A	68	83	110	m ohm
		V _{GS} =-3.1V , I _D =-1.4A	74	90	121	m ohm
		V _{GS} =-2.5V , I _D =-1.4A	82	102	138	m ohm
g _{FS}	Forward Transconductance	V _{DS} =-5V , I _D =-1.4A		6		S
DYNAMIC CHARACTERISTICS °						
C _{iss}	Input Capacitance	V _{DS} =-10V,V _{GS} =0V f=1.0MHz		347		pF
C _{OSS}	Output Capacitance			100		pF
C _{RSS}	Reverse Transfer Capacitance			81		pF
SWITCHING CHARACTERISTICS °						
t _{D(ON)}	Turn-On Delay Time	V _{DD} =-16V I _D =-1.4A V _{GS} =-4.5V R _{GEN} = 6 ohm		17		ns
t _r	Rise Time			30		ns
t _{D(OFF)}	Turn-Off Delay Time			15		ns
t _f	Fall Time			8.3		ns
Q _g	Total Gate Charge	V _{DS} =-16V,I _D =-2.8A, V _{GS} =-4.5V		5		nC
Q _{gs}	Gate-Source Charge			0.4		nC
Q _{gd}	Gate-Drain Charge			2.2		nC
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
V _{SD}	Diode Forward Voltage	V _{GS} =0V,I _S =-0.5A		-0.8	-1.2	V
Notes						
a.Surface Mounted on FR4 Board,t ≤ 10sec.						
b.Pulse Test:Pulse Width ≤ 10us, Duty Cycle ≤ 1%.						
c.Guaranteed by design, not subject to production testing.						

Sep,14,2012

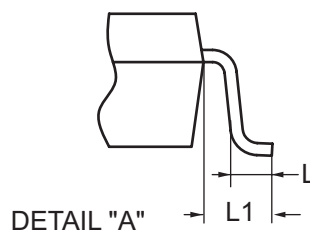
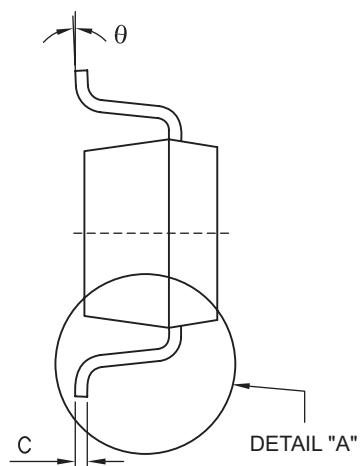
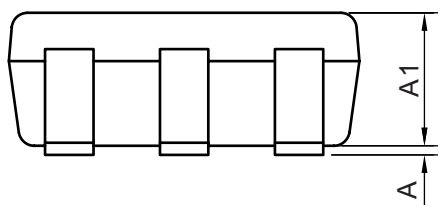
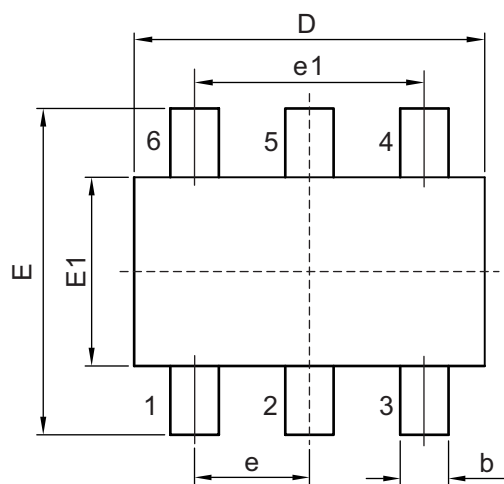






PACKAGE OUTLINE DIMENSIONS

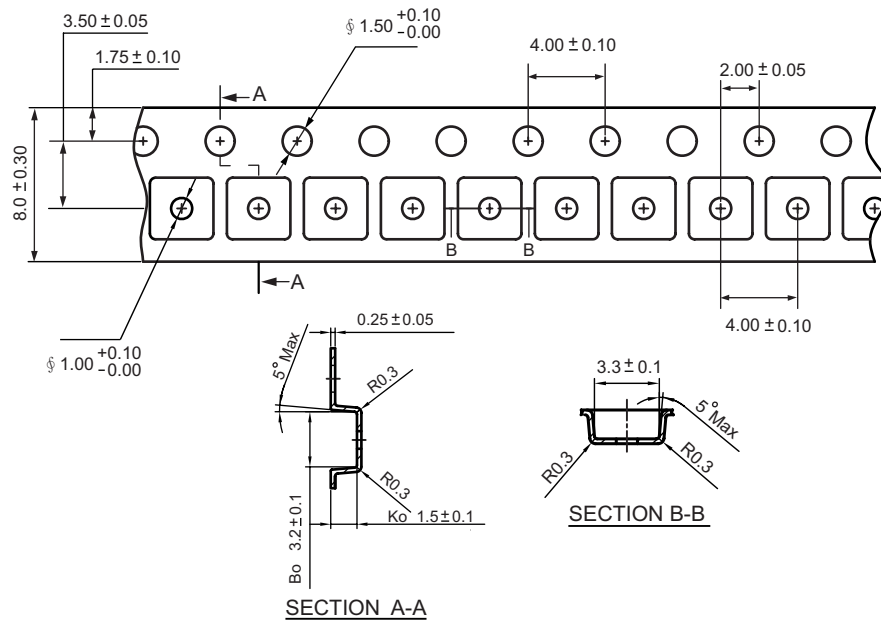
TSOT 26



SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
D	2.692	3.099	0.106	0.122
E	2.591	3.000	0.102	0.118
E1	1.397	1.803	0.055	0.071
e	0.950 REF.		0.037 REF.	
e1	1.900 REF.		0.075 REF.	
b	0.300	0.500	0.012	0.020
C	0.080	0.200	0.003	0.008
A	0.000	0.100	0.000	0.004
A1	0.700	0.800	0.028	0.032
L	0.300	0.600	0.012	0.024
L1	0.600 REF.		0.023 REF.	
θ	0°	6°	0°	6°

TSOT 26 Tape and Reel Data

TSOT 26 Carrier Tape



TSOT 26 Reel

